MOS FET

FL6L52010L

Panasonic

FL6L52010L

Silicon P-channel MOSFET(FET) Silicon epitaxial planar type(SBD)

For switching For DC-DC Converter

■ Features

- Low drain-source ON resistance : RDS (on) typ. = 80 m Ω (VGS = -4.0 V)
- Low drive voltage : 1.8 V drive
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol : Y1

Established: 2010-09-17

: 2013-10-17

Revised

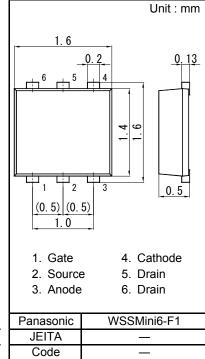
■ Packaging

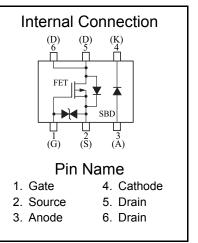
Embossed type (Thermo-compression sealing) 10 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

		Symbol	Rating	Unit	
FET	Drain to Source Voltage	VDS	-20	V	
	Gate to Source Voltage	VGS	±10	V	
	Drain current	ID	-2.0	Α	
	Peak drain current	IDp	-8.0	Α	
	Channel temperature	Tch	150	°C	
SBD	Reverse voltage	VR	20	V	
	Forward current (Average)	IF(AV)	800	mA	
	Junction temperature	Tj	125	°C	
Overall	Operating ambient temperature	Topr	-40 to +85	°C	
	Storage temperature	Tstg	-55 to +125	°C	
	Total power dissipation *1	PD	540	mW	

Note: *1 Measuring on ceramic substrate at 40 mm × 38 mm × 0.2 mm
PD absolute maximum rating without a heat shink: 150 mW





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■ Electrical Characteristics Ta = 25 °C ± 3 °C FET (P-ch.)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	VDSS	ID = -1.0 mA, VGS = 0	-20			V
Drain-source cutoff current	IDSS	VDS = -20 V, VGS = 0			-1.0	μA
Gate-source cutoff current	IGSS	$VGS = \pm 8 \text{ V, VDS} = 0$			±10	μA
Gate threshold voltage	VTH	ID = -1.0 mA, VDS = -10 V	-0.4	-0.75	-1.1	V
	RDS(on)1	ID = -1.0 A, VGS = -4.0 V		80	120	
Drain-source ON resistance *1	RDS(on)2	ID = -1.0 A, VGS = -2.5 V		100	170	mΩ
	RDS(on)3	ID = -0.5 A, VGS = -1.8 V		140	230	
Forward transfer admittance *1	Yfs	ID = -1.0 A, VDS = -10 V, f = 1 kHz	3.0			S
Short-circuit input capacitance (Common source)	Ciss			300		
Short-circuit output capacitance (Common source)	Coss	VDS = -10 V, VGS = 0, f = 1 MHz		30		pF
Reverse transfer capacitance (Common source)	Crss			35		•
Turn-on delay time *2	td(on)	VDD = -10 V, VGS = 0 V to - 4 V		6		ns
Rise time *2	tr	ID = -1.0 A		8		115
Turn-off delay time *2	td(off)	VDD = -10 V, VGS = -4 V to 0 V		57		ns
Fall time *2	tf	ID = -1.0 A		55		115

1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors. Note:

SBD

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	VF	IF = 800 mA			0.47	V
Reverse current	IR	VR = 20 V			80	μA

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for diodes.

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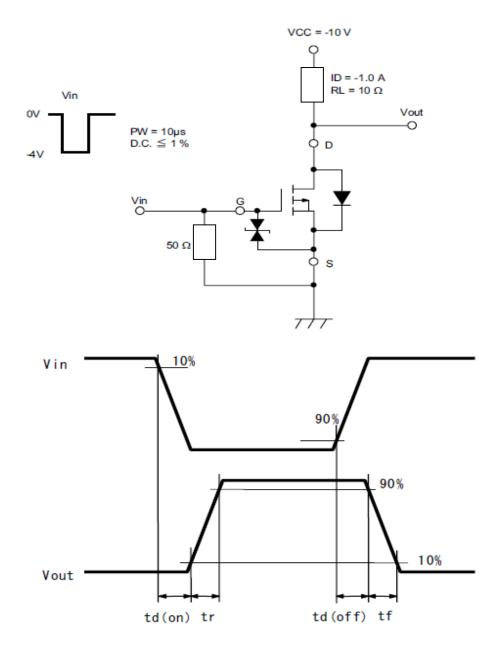
^{2. *1} Pulse measurement

^{*2} Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

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*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



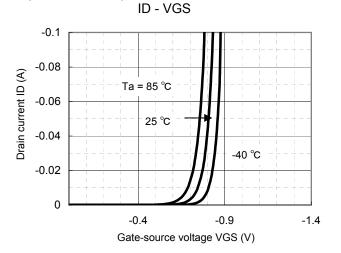
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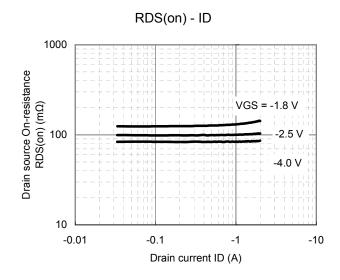
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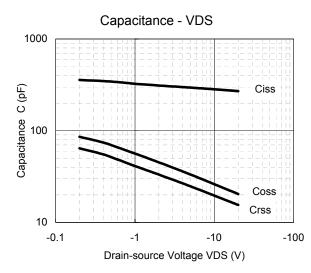
Technical Data (reference)

ID - VDS -2 -4.0 V -1.8 -1.6 Drain current ID (A) -1.4 -1.2 -1 -0.8 -0.6 -0.4 VGS= -1.0 V -0.2 0 0 -0.2 -0.4 -0.6 Drain-source voltage VDS (V)



VDS - VGS -1.8 -1.6 Drain-source voltage VDS (V) -1.4 -1.2 -1 ID=-2 mA-0.8 -1 mA -0.6 -0.4 -0.5 mA -0.2 0 -2 0 -4 -6





Gate-source voltage VGS (V)

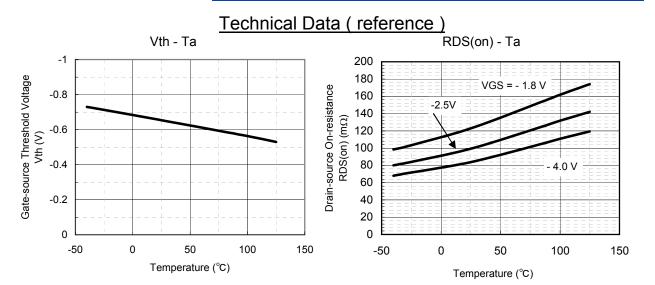
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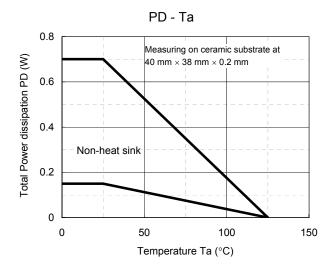
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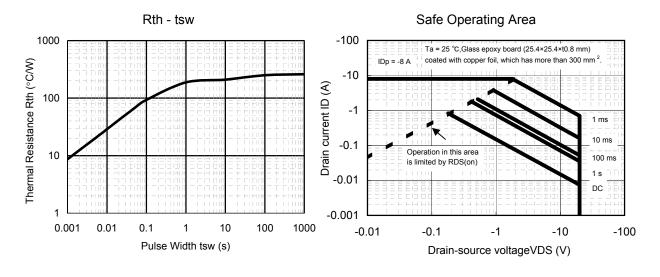
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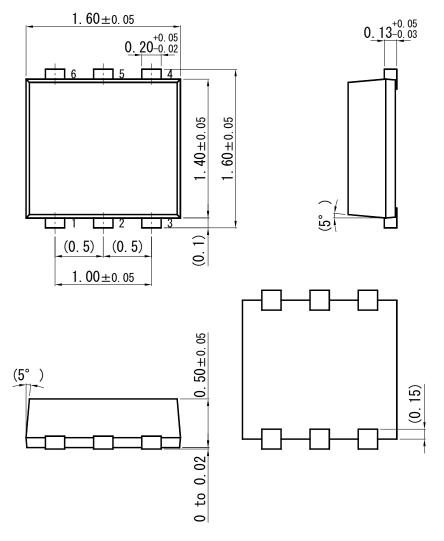
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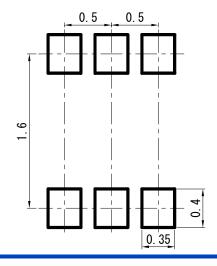
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WSSMini6-F1

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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